

DOCKET NO: 245469US2DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
TADASHI IGUCHI, ET AL. : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. APPLN. :
FILED: HEREWITH :
FOR: NONVOLATILE :
SEMICONDUCTOR MEMORY :
DEVICE AND ITS :
MANUFACTURING METHOD :

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to a first examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 7 of this paper.